



## NCE N-Channel Enhancement Mode Power MOSFET

#### Description

The NCE4080K uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

#### **General Features**

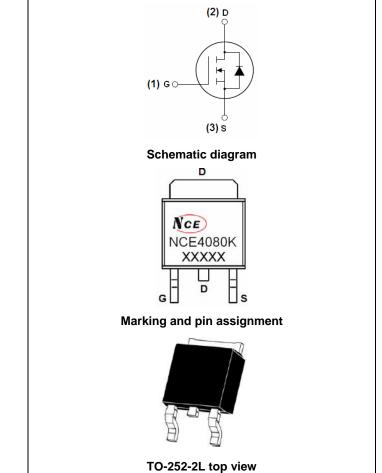
- V<sub>DS</sub> =40V,I<sub>D</sub> =80A
  R<sub>DS(ON)</sub> <7mΩ @ V<sub>GS</sub>=10V
  - $R_{DS(ON)}$  <15m $\Omega$  @ V<sub>GS</sub>=4.5V
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E<sub>AS</sub>
- Excellent package for good heat dissipation

#### Application

- PWM
- Load Switching

#### 100% UIS TESTED!

100% ΔVds TESTED!



#### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE4080K	NCE4080K	TO-252-2L	-	-	-

#### Absolute Maximum Ratings (T<sub>c</sub>=25℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	Vds	40	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Drain Current-Continuous	Ι <sub>D</sub>	80	А
Drain Current-Continuous(T <sub>C</sub> =100 ℃)	l <sub>D</sub> (100℃)	56	А
Pulsed Drain Current	I <sub>DM</sub>	350	A
Maximum Power Dissipation	PD	80	W
Derating factor		0.53	W/℃
Single pulse avalanche energy (Note 5)	E <sub>AS</sub>	750	mJ
Operating Junction and Storage Temperature Range	T <sub>J</sub> ,T <sub>STG</sub>	-55 To 175	°C





NCE4080K

#### **Thermal Characteristic**

Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup>	R <sub>θJC</sub>	1.88	°C/W
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#### Electrical Characteristics (T<sub>c</sub>=25<sup>°</sup>C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250µA	40	45	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =40V,V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	$V_{GS}$ =±20V, $V_{DS}$ =0V	-	-	±100	nA
On Characteristics (Note 3)	····		•			
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =250µA	1.2	1.8	2.5	V
Durain Course On State Desistance	P	$V_{GS}$ =10V, I <sub>D</sub> =20A	-	5.2	7	mΩ
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =20A	-	10	15	mΩ
Forward Transconductance	<b>G</b> FS	V <sub>DS</sub> =10V,I <sub>D</sub> =20A	15	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C <sub>lss</sub>	N/ 00)/// 0)/	-	2662	3200	PF
Output Capacitance	Coss	$V_{DS}$ =20V, $V_{GS}$ =0V,	-	322	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.0MHz	-	246	-	PF
Switching Characteristics (Note 4)			L			I.
Turn-on Delay Time	t <sub>d(on)</sub>		-	12	-	nS
Turn-on Rise Time	tr	$V_{DD}$ =20V, R <sub>L</sub> =1 $\Omega$	-	11	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =10V, $R_{G}$ =3 $\Omega$	-	39	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	12	-	nS
Total Gate Charge	Qg	N/ 00X/1 00A	-	54.3	-	nC
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS}=20V, I_{D}=20A,$	-	6.9	-	nC
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> =10V	-	14.5	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =10A	-		1.2	V
Diode Forward Current (Note 2)	Is		-	-	80	A
Reverse Recovery Time	t <sub>rr</sub>	TJ = 25°C, IF = 20A	-	-	45	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs <sup>(Note3)</sup>	-	-	50	nC

#### Notes:

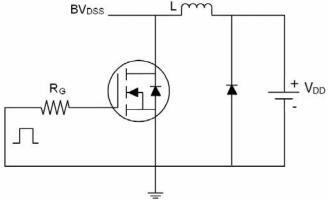
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board,  $t \le 10$  sec.
- **3.** Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2%.
- 4. Guaranteed by design, not subject to production
- 5.  $E_{AS}$  condition : Tj=25  $^\circ\!\!\!\mathrm{C}$  ,V\_{DD}=20V,V\_G=10V,L=1mH,Rg=25\Omega, ~I\_{AS}=42A



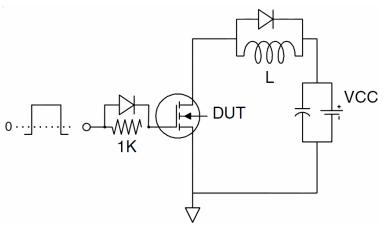
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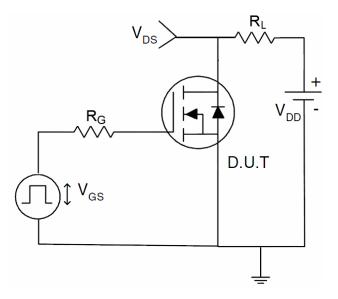
### Test circuit 1) E<sub>AS</sub> Test Circuit



2) Gate Charge Test Circuit



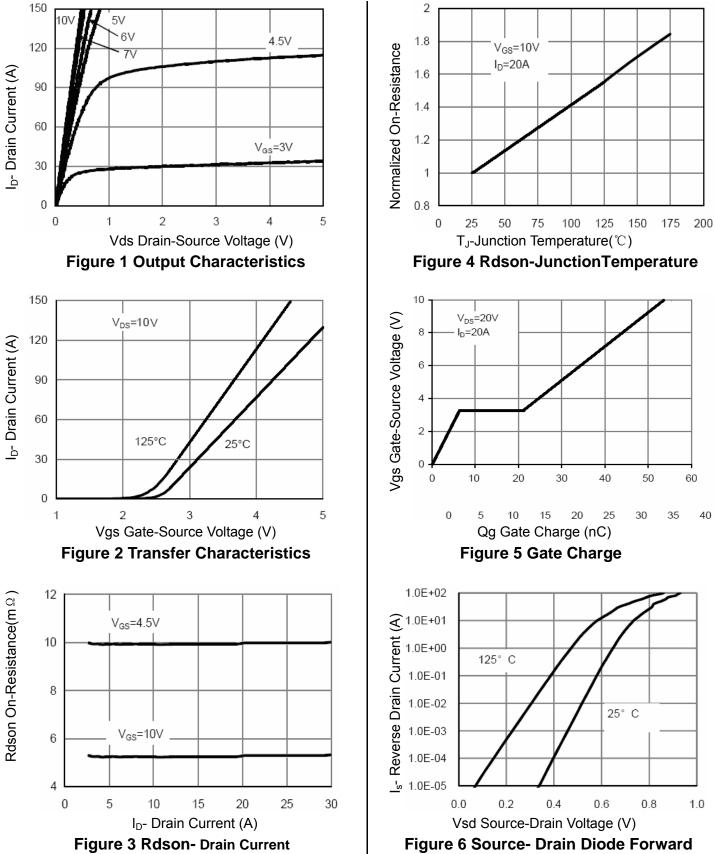
3) Switch Time Test Circuit







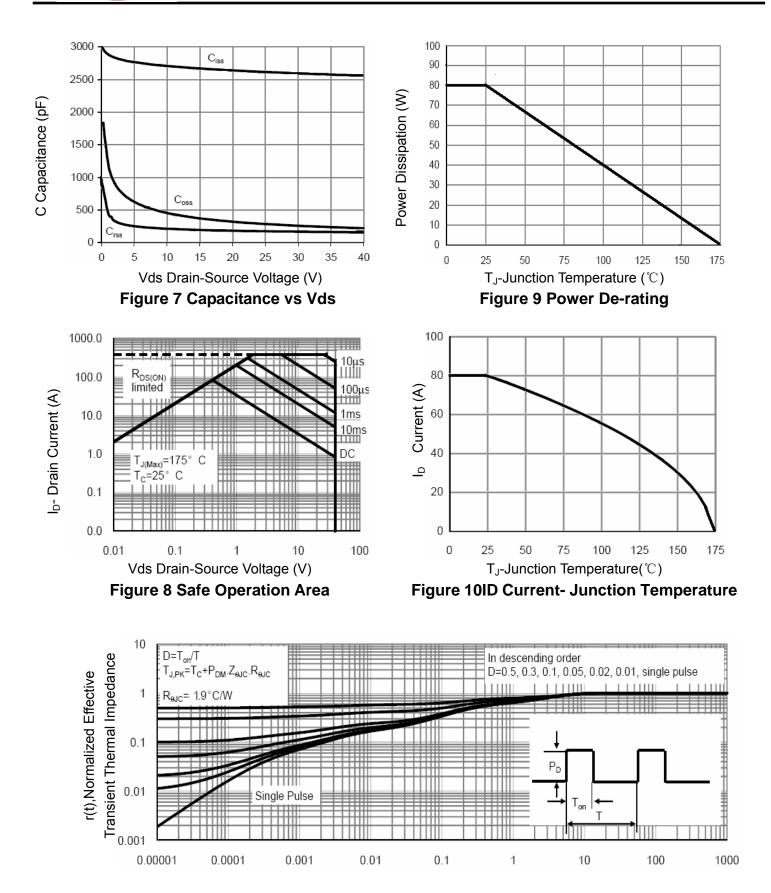






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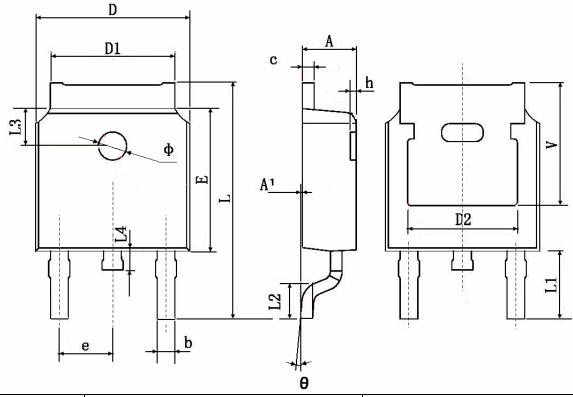
Square Wave Pluse Duration(sec) Figure 11 Normalized Maximum Transient Thermal Impedance



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# TO-252 Package Information



Symbol	Dimensions	n Millimeters	Dimensions In Inches		
	Min.	Max.	Min.	Max.	
A	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.660	0.860	0.026	0.034	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	4.8	330 TYP.	0.190 TYP.		
E	6.000	6.200	0.236	0.244	
e	2.186	2.386	0.086	0.094	
L	9.800	10.400	0.386	0.409	
L1	2.900	2.900 TYP.		TYP.	
L2	1.400	1.700	0.055	0.067	
L3	1.600	TYP.	0.063 TYP.		
L4	0.600	1.000	0.024	0.039	
Φ	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.350	TYP.	0.211 TYP.		

Remark: 由于有多家封装合格供应商,在封装外形有略微差异,脚间距符合JEDEC标准。





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